

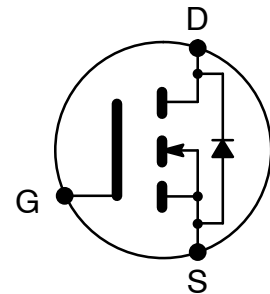


ELECTRONICS, INC.  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089  
<http://www.nteinc.com>

## NTE2960 MOSFET N-Channel, Enhancement Mode High Speed Switch TO-220 Full Pack Type Package

**Applications:**

- SMPS
- DC-DC Converter
- Battery Charger
- Power Supply of Printer
- Copier
- HDD, FDD, TV, VCR
- Personal Computer



**Absolute Maximum Ratings:** ( $T_C = +25^\circ\text{C}$  unless otherwise specified)

Drain-Source Voltage ( $V_{GS} = 0\text{V}$ ), $V_{DSS}$ .....	900V
Gate-Source Voltage ( $V_{DS} = 0\text{V}$ ), $V_{GS}$ .....	$\pm 30\text{V}$
Drain Current, $I_D$	
Continuous .....	7A
Pulsed .....	21A
Maximum Power Dissipation, $P_D$ .....	40W
Channel Temperature Range, $T_{ch}$ .....	$-55^\circ$ to $+150^\circ\text{C}$
Storage Temperature Range, $T_{stg}$ .....	$-55^\circ$ to $+150^\circ\text{C}$
Thermal Resistance, Channel-to-Case, $R_{th(ch-c)}$ .....	$3.13^\circ\text{C/W}$
Isolation Voltage, $V_{ISO}$ .....	2000V

**Electrical Characteristics:** ( $T_{ch} = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{V}$ , $I_D = 1\text{mA}$	900	-	-	V
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$V_{DS} = 0\text{V}$ , $I_G = \pm 100\mu\text{A}$	$\pm 30$	-	-	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 25\text{V}$ , $V_{DS} = 0\text{V}$	-	-	$\pm 10$	$\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 900\text{V}$ , $V_{GS} = 0$	-	-	1.0	mA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = 10\text{V}$ , $I_D = 1\text{mA}$	2.0	3.0	4.0	V
Static Drain-Source ON Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$ , $I_D = 3\text{A}$	-	1.54	2.00	$\Omega$
Drain-Source On-State Voltage	$V_{DS(on)}$	$V_{GS} = 10\text{V}$ , $I_D = 3\text{A}$	-	4.62	6.00	V
Forward Transfer Admittance	$ y_{fs} $	$V_{GS} = 10\text{V}$ , $I_D = 3\text{A}$	4.2	7.0	-	S

**Electrical Characteristics (Cont'd):** ( $T_{ch} = +25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$	-	1380	-	pF
Output Capacitance	$C_{oss}$		-	140	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	28	-	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 200\text{V}, I_D = 3\text{A}, V_{GS} = 10\text{V}, R_{GEN} = R_{GS} = 50\Omega$	-	25	-	ns
Rise Time	$t_r$		-	28	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	185	-	ns
Fall Time	$t_f$		-	46	-	ns
Diode Forward Voltage	$V_{SD}$	$I_S = 3\text{A}, V_{GS} = 0\text{V}$	-	1.0	1.5	V

